# **QUALIFICATION REPORT**

# EPC eGaN<sup>®</sup> FET Qualification Report EPC2055



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This report summarizes the Product Qualification results for EPC part number EPC2055 which meets all required qualification requirements and is released for production.

#### Scope

The testing matrix in this qualification report covers the qualification of EPC2055. For some tests, EPC2055 was qualified by matrix with EPC2204 and EPC2218. All three products are compared in the table below. EPC2055 has the same die size, packaging process and bump design as EPC2204. EPC2218 has same packaging process as EPC2055 and EPC2204, but has larger die size.

Part Number	Voltage (V)	R <sub>DS(on)</sub> (mΩ)	Die Size (mm x mm)
EPC2218	100	3.2	L (3.5 x 1.95)
EPC2204	100	6	S (2.5 x 1.5)
EPC2055	40	3.6	S (2.5 x 1.5)

# **Qualification Test Overview**

EPC's eGaN FETs were subjected to a wide variety of stress tests under conditions that are typical for silicon-based power MOSFETs. These tests included:

- High temperature reverse bias (HTRB): Parts are subjected to a drainsource voltage at the maximum rated temperature
- High temperature gate bias (HTGB): Parts are subjected to a gatesource voltage at the maximum rated temperature
- High temperature storage (HTS): Parts are subjected to heat at the maximum rated temperature
- Temperature cycling (TC): Parts are subjected to alternating highand low temperature extremes
- High temperature high humidity reverse bias (H3TRB): Parts are subjected to humidity under high temperature with a drain-source voltage applied
- Moisture sensitivity level (MSL): Parts are subjected to moisture, temperature, and three cycles of reflow

The stability of the devices is verified with DC electrical tests after stress biasing. The electrical parameters are measured at time-zero and at interim readout points at room temperature. Electrical parameters such as the gate-source leakage, drain-source leakage, gate-source threshold voltage, and on-state resistance are compared against the data sheet specifications. A failure is recorded when a part exceeds the datasheet specifications. eGaN FETs are stressed to meet the latest Joint Electron Device Engineering Council (JEDEC) standards when possible.

Parts for all tests except for TC were mounted onto FR5 (high Tg FR4) or polyimide adaptor cards. Adaptor cards of 1.6 mm in thickness with two copper layers were used. The top copper layer was 1 oz. or 2 oz., and the bottom copper layer was 1 oz. Kester NXG1 type 3 SAC305 solder no clean flux was used in mounting the part onto an adaptor card.

## **High Temperature Reverse Bias**

Parts were subjected to 80% of the rated drain-source voltage at the maximum rated temperature for a stress period of 1000 hours.

Stress Test	Part Number	Voltage (V)	Die Size (mm x mm)	Test Condition	# of Failure	Sample Size (unit x lot)	Duration (Hrs)
HTRB	EPC2055	40	S (2.5 x 1.5)	$T = 150^{\circ}C, V_{DS} = 32 V$	0	77 x 1	1000
HTRB	EPC2055	40	S (2.5 x 1.5)	$T = 150^{\circ}C, V_{DS} = 32 V$	0	77 x 1	1000
HTRB	EPC2055	40	S (2.5 x 1.5)	$T = 150^{\circ}C, V_{DS} = 32 V$	0	77 x 1	1000

Table 1. High Temperature Reverse Bias Test

#### **High Temperature Gate Bias**

Parts were subjected to 6.0 V gate-source bias at the maximum rated temperature for a stress period of 1000 hours.

Stress Test	Part Number	Voltage (V)	Die Size (mm x mm)	Test Condition	# of Failure	Sample Size (unit x lot)	Duration (Hrs)
HTGB	EPC2055	40	S (2.5 x 1.5)	$T = 150^{\circ}C, V_{GS} = 6 V$	0	77 x 1	1000
HTGB	EPC2055	40	S (2.5 x 1.5)	$T = 150^{\circ}C, V_{GS} = 6 V$	0	77 x 1	1000
HTGB	EPC2055	40	S (2.5 x 1.5)	$T = 150^{\circ}C, V_{GS} = 6 V$	0	77 x 1	1000

Table 2. High Temperature Gate Bias Test

#### **High Temperature Storage**

Parts were subjected to heat at the maximum rated temperature.

Stress Test	Part Number	Voltage (V)	Die Size (mm x mm)	Test Condition	# of Failure	Sample Size (unit x lot)	Duration (Hrs)
HTS	EPC2055	40	S (2.5 x 1.5)	T = 150°C, Air	0	77 x 1	1000
HTS	EPC2055	40	S (2.5 x 1.5)	T = 150°C, Air	0	77 x 1	1000
HTS	EPC2055	40	S (2.5 x 1.5)	T = 150°C, Air	0	77 x 1	1000

Table 3. High Temperature Storage Test

#### **Temperature Cycling**

As seen in Table 4, two lots (77 parts each) of EPC2055 were tested on PCB (Arlon 85NT), passing 1000 cycles of -40 to 125°C. In addition, three lots of EPC2218 were temperature cycled in bare die form, passing 850 cycles. EPC2218 has the same packaging process as EPC2055, but is significantly larger. For all tests, parts were subjected to temperature cycling between -40°C and +125°C, with dwell time of 10 minutes and 2 cycles/hour in accordance with the JEDEC Standard JESD22A104.

Stress Test	Part Number	Voltage (V)	Die Size (mm x mm)	Test Condition	# of Failure	Sample Size (unit x lot)	Duration (Cys)
TC	EPC2218	100	L (3.5 x 1.95)	-40 to +125°C, Air	0	77 x 1	850
TC	EPC2218	100	L (3.5 x 1.95)	-40 to +125°C, Air	0	77 x 1	850
TC	EPC2218	100	L (3.5 x 1.95)	-40 to +125°C, Air	0	77 x 1	850
TC	EPC2055	40	S (2.5 x 1.5)	-40 to +125°C, Air	0	77 x 1	1000
TC	EPC2055	40	S (2.5 x 1.5)	-40 to +125°C, Air	0	77 x 1	1000

Table 4. Temperature Cycling Test

## High Temperature High Humidity Reverse Bias

Parts were subjected to a drain-source bias at 85% RH and 85°C for a stress period of 500 hours. The testing was done in accordance with the JEDEC Standard JESD22A101.

Stress Test	Part Number	Voltage (V)	Die Size (mm x mm)	Test Condition	# of Failure	Sample Size (unit x lot)	Duration (Hrs)
H3TRB	EPC2055	40	S (2.5 x 1.5)	$T = 85^{\circ}C, RH = 85\%, V_{DS} = 32 V$	0	77 x 1	1000
H3TRB	EPC2055	40	S (2.5 x 1.5)	$T = 85^{\circ}C, RH = 85\%, V_{DS} = 32 V$	0	77 x 1	1000
H3TRB	EPC2055	40	S (2.5 x 1.5)	T = 85°C, RH = 85%, V <sub>DS</sub> = 32 V	0	77 x 1	1000

Table 5. High Temperature High Humidity Reverse Bias Test

## **Moisture Sensitivity Level**

EPC2055 is qualified by matrix with EPC2218 and EPC2204. Parts were subjected to 85% RH at 85°C for a stress period of 168 hours. The parts were also subjected to three cycles of Pb-free reflow in accordance with the IPC/JEDEC joint Standard J-STD-020.

Stress Test	Part Number	Voltage (V)	Die Size (mm x mm)	Test Condition	# of Failure	Sample Size (unit x lot)	Duration (Hrs)
MSL1	EPC2218	100	L (3.5 x 1.95)	T = 85°C, RH = 85%, 3 reflow	0	77 x 1	168
MSL1	EPC2218	100	L (3.5 x 1.95)	T = 85°C, RH = 85%, 3 reflow	0	77 x 1	168
MSL1	EPC2204	100	S (2.5 x 1.5)	T = 85°C, RH = 85%, 3 reflow	0	77 x 1	168

Table 6. Moisture Sensitivity Level Test